

NJ450L Process

Silicon Junction Field-Effect Transistor

- Low-Current
- Low Gate Leakage Current
- High Input Impedance

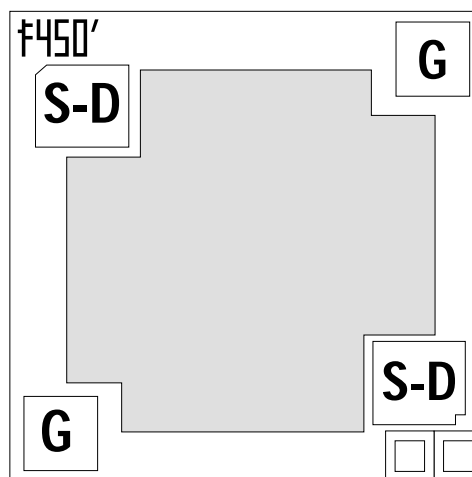
Absolute maximum ratings at 25 °C free-air temperature.

Gate Current, I_G	10 mA
Operating Junction Temperature, T_j	+150°C
Storage Temperature, T_s	- 65°C to +175°C

Devices in this Databook based on the NJ450L Process.

Datasheet

2N6550
IF4500
IF4501
IFN860



Die Size = 0.028" X 0.028"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

At 25°C free air temperature:

Static Electrical Characteristics

		NJ450L Process						
		Min	Typ	Max	Unit	Test Conditions		
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	- 25	- 25		V	$I_G = - 1 \mu A, V_{DS} = 0V$		
Reverse Gate Leakage Current	I_{GSS}		- 50		pA	$V_{GS} = - 15V, V_{DS} = 0V$		
Drain Saturation Current (Pulsed)	I_{DSS}	5			mA	$V_{DS} = 15V, V_{GS} = 0V$		
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	- 0.1		- 4	V	$V_{DS} = 15V, I_D = 1 nA$		

Dynamic Electrical Characteristics

Forward Transconductance (Pulsed)	g_{fs}		100		mS	$V_{DS} = 15V, V_{GS} = 0V$	$f = 1 kHz$
Input Capacitance	C_{iss}		35		pF	$V_{DS} = 0V, V_{GS} = - 10V$	$f = 1 MHz$
Feedback Capacitance	C_{rss}		10		pF	$V_{DS} = 0V, V_{GS} = - 10V$	$f = 1 MHz$
Equivalent Noise Voltage	\hat{e}_N		0.9		nV/ \sqrt{HZ}	$V_{DG} = 4V, I_D = 5 mA$	$f = 1 kHz$



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